SCLS104B - MARCH 1984 - REVISED MAY 1997

- High-Current 3-State Outputs Interface Directly With System Bus or Can Drive up to 15 LSTTL Loads
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) 300-mil DIPs

description

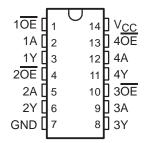
These quadruple bus buffer gates feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

The SN54HC125 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74HC125 is characterized for operation from –40°C to 85°C.

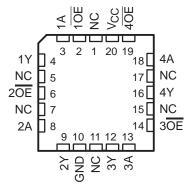
FUNCTION TABLE (each buffer)

INP	JTS	OUTPUT
OE	Α	Y
L	Н	Н
L	L	L
н	Χ	Z

SN54HC125 . . . J OR W PACKAGE SN74HC125 . . . D, DB, OR N PACKAGE (TOP VIEW)

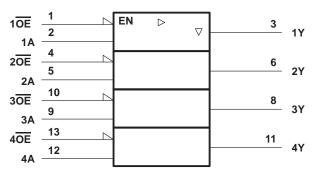


SN54HC125 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, J, N, and W packages.



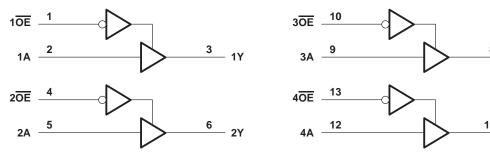
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SN54HC125, SN74HC125 **QUADRUPLE BUS BUFFER GATES** WITH 3-STATE OUTPUTS

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logic diagram (positive logic)



Pin numbers shown are for the D, DB, J, N, and W packages.

absolute maximum ratings over operating free-air temperature range

Supply voltage range, V _{CC}		0.5 V to 7 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) (see		
Output clamp current, IOK (VO < 0 or VO > VC	C) (see Note 1)	±20 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC})		±35 mA
Continuous current through V _{CC} or GND		±70 mA
Package thermal impedance, θ _{JA} (see Note 2)	: D package	127°C/W
	DB package	158°C/W
	N package	
Storage temperature range, T _{sta}		

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

recommended operating conditions

			SI	154HC12	25	SI	SN74HC125		
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Vcc	Supply voltage		2	5	6	2	5	6	V
		V _{CC} = 2 V	1.5			1.5			
V_{IH}	High-level input voltage	V _{CC} = 4.5 V	3.15			3.15			V
		V _{CC} = 6 V	4.2			4.2		0.5 1.35 V 1.8 VCC V	
		V _{CC} = 2 V	0		0.5	0		0.5	
V_{IL}	Low-level input voltage	$V_{CC} = 4.5 \text{ V}$	0		1.35	0		1.35	V
		V _{CC} = 6 V	0		1.8	0		1.8	
٧ _I	Input voltage		0		VCC	0		VCC	V
٧o	Output voltage		0		VCC	0		VCC	V
		V _{CC} = 2 V	0		1000	0		1000	
t _t	Input transition (rise and fall) time	$V_{CC} = 4.5 \text{ V}$	0		500	0		500	ns
		V _{CC} = 6 V	0		400	0		400	
T _A	Operating free-air temperature		-55	•	125	-40	•	85	°C



^{2.} The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CO	TEST CONDITIONS		Т	A = 25°C	;	SN54HC125		SN74HC125		UNIT
PARAMETER	1231 CC	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT	
			2 V	1.9	1.998		1.9		1.9		
		I _{OH} = -20 μA	4.5 V	4.4	4.499		4.4		4.4		
Voн	$V_I = V_{IH} \text{ or } V_{IL}$		6 V	5.9	5.999		5.9		5.9		V
		I _{OH} = -6 mA	4.5 V	3.98	4.3		3.7		3.84		
		$I_{OH} = -7.8 \text{ mA}$	6 V	5.48	5.8		5.2		5.34		
	VI = VIH or VIL		2 V		0.002	0.1		0.1		0.1	
		I _{OL} = 20 μA	4.5 V		0.001	0.1		0.1		0.1	
VOL			6 V		0.001	0.1		0.1		0.1	V
		$I_{OL} = 6 \text{ mA}$	4.5 V		0.17	0.26		0.4		0.33	
		$I_{OL} = 7.8 \text{ mA}$	6 V		0.15	0.26		0.4		0.33	
lį	$V_I = V_{CC}$ or 0		6 V		±0.1	±100		±1000		±1000	nA
loz	$V_O = V_{CC}$ or 0		6 V		±0.01	±0.5		±10		±5	μΑ
Icc	$V_I = V_{CC}$ or 0,	I _O = 0	6 V			8		160		80	μΑ
Ci			2 V to 6 V		3	10		10		10	pF

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	Vaa	T,	λ = 25°C	;	SN54H	IC125	SN74H	C125	UNIT		
PARAMETER	(INPUT)	(OUTPUT)	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT		
			2 V		48	120		150		150			
t _{pd}	А	Υ	4.5 V		14	24		36		30	ns		
			6 V		11	20		25		26			
			2 V		53	120		180		150			
t _{en}	ŌĒ	Y	Y	4.5 V		14	24		36		30	ns	
				6 V		11	20		31		26		
			2 V		30	120		180		150			
^t dis	ŌĒ	Υ	Υ	Υ	4.5 V		15	24		36		30	ns
			6 V		14	20		31		26			
	А	Any	2 V		28	60		90		75			
t _t			4.5 V		8	12		18		15	ns		
			6 V		6	10		15		13			

SN54HC125, SN74HC125 QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

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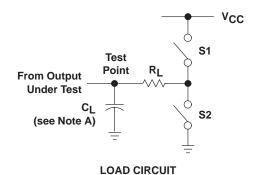
switching characteristics over recommended operating free-air temperature range, C_L = 150 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	FROM TO		T,	ղ = 25°C	;	SN54H	C125	SN74H	C125	UNIT																					
FARAWIETER	(INPUT)	(OUTPUT)	(OUTPUT)	(OUTPUT)	(OUTPUT)	(OUTPUT)	VCC	MIN	TYP	MAX	MIN	MAX	MIN	MAX	ONIT																	
			2 V		67	150		225		190																						
t _{pd}	А	Y	Y	Y	4.5 V		19	30		45		38	ns																			
								ľ	ľ	ľ		Ī	Ī			ľ											6 V		15	25		39
			2 V		100	135		200		170																						
t _{en}	ŌĒ	Y	Υ	4.5 V		20	27		40		34	ns																				
			6 V		17	23		34		29																						
			2 V		45	210		315		265																						
t _t		Any	4.5 V		17	42		63		53	ns																					
			6 V		13	36		53		45																						

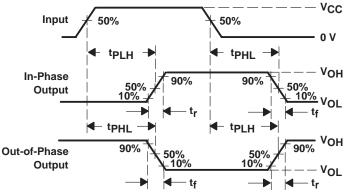
operating characteristics, $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance per gate	No load	45	pF

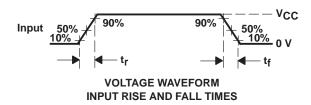
PARAMETER MEASUREMENT INFORMATION

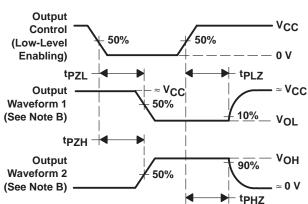


PARAI	PARAMETER		CL	S1	S2	
	tPZH 1 kΩ		50 pF or	Open	Closed	
ten	tPZL	1 K22	150 pF	Closed	Open	
4	tPHZ	1 k Ω	50 pF	Open	Closed	
^t dis	tPLZ	1 K22	30 pr	Closed	Open	
t _{pd} or t _t		_	50 pF or 150 pF	Open	Open	



VOLTAGE WAVEFORMS
PROPAGATION DELAY AND OUTPUT TRANSITION TIMES





VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES FOR 3-STATE OUTPUTS

- NOTES: A. C_L includes probe and test-fixture capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_O = 50 \Omega$, $t_r = 6 \text{ ns}$.
 - D. The outputs are measured one at a time with one input transition per measurement.
 - E. tpLZ and tpHZ are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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